

具有 AGC 和 RSSI 的 4.25-Gbps 互阻抗放大器

 查询样品: [ONET4291T](#)

特性

- **2.8 GHz** 带宽
- **3.2 k Ω** 差分互阻抗
- 自动增益控制 (**AGC**)
- 典型值为 **8.8-pA/ $\sqrt{\text{Hz}}$** 的输入参考噪声
- **2-mA_{p-p}** 最大输入电流
- 接收信号强度指示 (**RSSI**)
- 支持片上 **50 Ω** 背向端接的 **CML** 数据输出
- 片上电源滤波器电容器
- **3.3 V** 单电源
- 芯片大小: **0.78 × 1.18 mm**

应用

- **OC24** 与 **OC48** 标准下的 **SONET/SDH** 传输系统
- **4.25 Gbps**、**2.125 Gbps** 与 **1.0625 Gbps** 的光纤通道接收器
- 千兆位以太网接收器
- **PIN** 前置放大器接收器

说明

ONET4291T 是一款高速互阻抗放大器，适用于数据传输速率高达 4.25 Gbps 的光电接收器。

它支持低输入参考噪声、2.8 GHz 带宽、自动增益控制 (AGC)、3.2 k Ω 互阻抗以及接收信号强度指示 (RSSI)。

ONET4291T 采用裸片封装，针对 TO can 应用进行了优化。

ONET4291T 采用 3.3 V 单电源供电，其低功耗设计通常支持不足 56 mW 的功耗。该器件可在 -40°C 至 85°C 环境下平稳工作。

提供的选项

T _A	DIE
-40°C 至 85°C	ONET4291TY



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

BLOCK DIAGRAM

The ONET4291T is a high-performance, 4.25-Gbps transimpedance amplifier consisting of the signal path, supply filter, a control block for dc input current cancellation, automatic gain control (AGC), received signal strength indication (RSSI), and a band-gap voltage reference and bias current generation block.

The signal path comprises a transimpedance amplifier stage, a voltage amplifier, and a CML output buffer.

The on-chip filter circuit provides filtered V_{CC} for the photodiode and for the transimpedance amplifier. The dc input current cancellation and AGC use internal low-pass filters to cancel the dc current on the input and to adjust the transimpedance amplifier gain. Furthermore, circuitry to monitor the received signal strength is provided.

A simplified block diagram of the ONET4291T is shown in Figure 1.

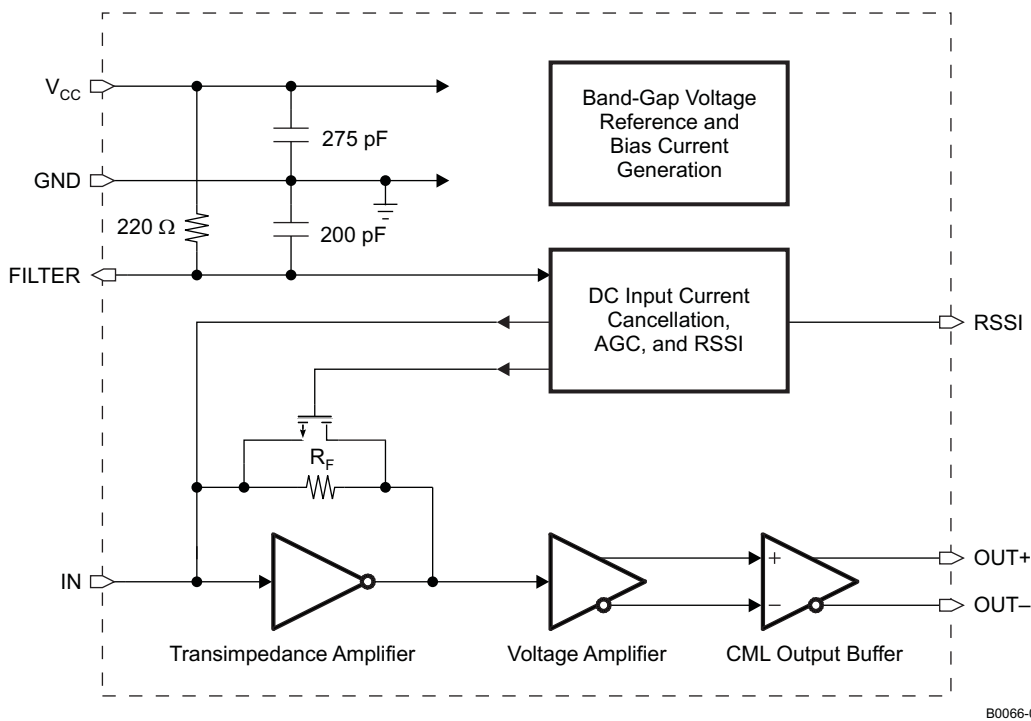


Figure 1. Simplified Block Diagram of the ONET4291T

SIGNAL PATH

The first stage of the signal path is a transimpedance amplifier that takes the photodiode current and converts it into a voltage signal.

If the input signal current exceeds a certain value, the transimpedance gain is reduced by means of AGC circuitry.

The second stage is a voltage amplifier that provides additional gain and converts its single-ended input voltage into a differential data signal.

The third signal-path stage is the output buffer, which provides CML outputs with on-chip, 50-Ω back-termination to V_{CC} .

FILTER CIRCUITRY

The filter pin provides filtered V_{CC} for the photodiode bias. The on-chip, low-pass filter for the photodiode V_{CC} is implemented using a filter resistor of 220 Ω and an internal 200-pF capacitor. The corresponding corner frequency is below 4 MHz.

The supply voltage for the whole amplifier is filtered by means of an on-chip, 275-pF capacitor as well, thus avoiding the necessity to use an external supply-filter capacitor.

DC INPUT CURRENT CANCELLATION, AGC, AND RSSI

The voltage drop across the internal photodiode supply-filter resistor is monitored by means of a dc input current cancellation, AGC, and RSSI control circuit block.

If the dc input current exceeds a certain level, it is partially cancelled by means of a controlled current source. This measure keeps the transimpedance amplifier stage within sufficient operating point limits for optimum performance. Furthermore, disabling the dc input cancellation at low input currents leads to superior noise performance.

The AGC circuitry lowers the effective transimpedance feedback resistor R_F by means of a MOSFET device acting as a controlled shunt. This prevents the transimpedance amplifier from being overdriven at high input currents, which leads to improved jitter behavior within the complete input-current dynamic range. Because the voltage drop across the supply-filter resistor is sensed and used by the AGC circuit, the photodiode must be connected to a FILTER pad for the AGC to function correctly.

Finally, this circuit block senses the current through the filter resistor and generates a mirrored current, which is proportional to the input signal strength. The mirrored current is available at the RSSI output and must be sunk to ground (GND) using an external resistor. The RSSI gain can be adjusted by choosing the external resistor; however, for proper operation, ensure that the voltage at the RSSI pad never exceeds $V_{CC} - 0.65$ V.

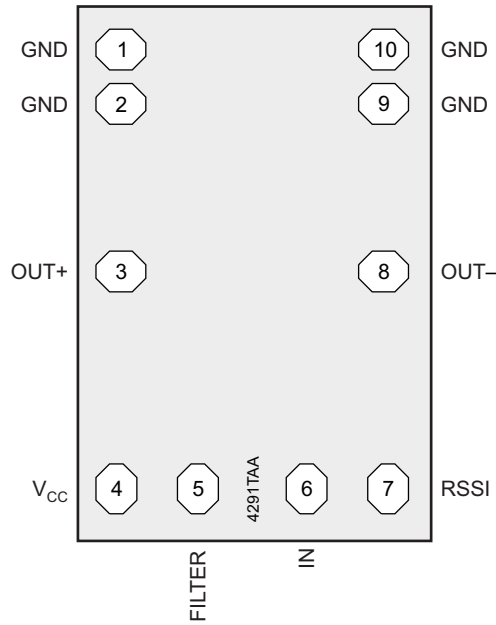
BAND-GAP VOLTAGE AND BIAS GENERATION

The ONET4291T transimpedance amplifier is supplied by a single, 3.3-V supply voltage connected to the V_{CC} pad. This voltage is referred to GND.

On-chip band-gap voltage circuitry generates a supply-voltage-independent reference from which all other internally required voltages and bias currents are derived.

BOND PAD ASSIGNMENT

The ONET4291T is available as a bare die. The locations of the bond pads are shown in the following figure.



M0033-04

BOND PAD DESCRIPTION

PAD		TYPE	DESCRIPTION
NAME	NO.		
FILTER	5	Analog	Bias voltage for photodiode (cathode). This pads connects through an internal 220-Ω resistor to V _{CC} and a 200-pF filter capacitor to ground (GND). The FILTER pad(s) must be connected to the photodiode for the AGC to function.
GND	1, 2, 9, 10	Supply	Circuit ground. All GND pads are connected on die. Bonding all pads is optional; however, for optimum performance a good ground connection is mandatory.
IN	6	Analog input	Data input to TIA (photodiode anode)
OUT+	3	Analog output	Non-inverted data output. On-chip 50-Ω back-terminated to V _{CC} .
OUT-	8	Analog output	Inverted data output. On-chip 50-Ω back-terminated to V _{CC} .
RSSI	7	Analog output	Analog output current proportional to the input data amplitude. Indicates the strength of the received signal (RSSI). Must be sunk through an external resistor to ground (GND). The RSSI gain can be adjusted by choosing the external resistor; however, for proper operation, ensure that the voltage at the RSSI pad never exceeds V _{CC} - 0.65 V. If the RSSI feature is not used, this pad must be bonded to ground (GND) to ensure proper operation.
V _{CC}	4	Supply	3.3-V, +10%/-12% supply voltage

ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

V_{CC}	Supply voltage ⁽²⁾	–0.3 V to 4 V
V_{FILTER} , V_{OUT+} , V_{OUT-} , V_{RSSI}	Voltage at FILTER, OUT+, OUT–, RSSI ⁽²⁾	–0.3 V to 4 V
I_{IN}	Current into IN	–0.7 mA to 2.5 mA
I_{FILTER}	Current into FILTER	– 8 mA to 8 mA
I_{OUT+} , I_{OUT-}	Continuous current at outputs	– 8 mA to 8 mA
ESD	ESD rating at all pins except IN ⁽³⁾	1.5 kV (HBM)
	ESD rating at IN ⁽³⁾	300 V (HBM)
$T_{J,max}$	Maximum junction temperature	125°C
T_{stg}	Storage temperature range	–65°C to 85°C
T_A	Operating free-air temperature range	–40°C to 85°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values are with respect to network ground terminal.

(3) For optimum high-frequency performance, the input pin has reduced ESD protection.

RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage	2.9	3.3	3.6	V
T_A	Operating free-air temperature	–40		85	°C
L_{FILTER} , L_{IN}	Wire-bond inductor at pins FILTER and IN			0.8	nH
C_{PD}	Photodiode capacitance		0.2		pF

DC ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted). Typical values are at $V_{CC} = 3.3$ V and $T_A = 25^\circ\text{C}$.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{CC}	Supply voltage		2.9	3.3	3.6	V
I_{VCC}	Supply current	Average photodiode current $I_{PD} = 0$ mA	11	17	25	mA
V_{IN}	Input bias voltage			0.85	1.05	V
R_{OUT}	Output resistance	Single-ended to V_{CC}	40	50	60	Ω
R_{FILTER}	Photodiode filter resistance			220		Ω

AC ELECTRICAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted). Typical values are at $V_{CC} = 3.3\text{ V}$ and $T_A = 25^\circ\text{C}$.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
i_{IN-OVL}	AC input overload current		2			mA_{p-p}
A_{RSSI}	RSSI gain	Resistive load to GND ⁽¹⁾	0.95	1	1.05	A/A
	RSSI output offset current (no light)			15	30	μA
Z_{21}	Small-signal transimpedance	Differential output; input current $i_{IN} = 50\ \mu\text{A}_{p-p}$	2300	3200	3900	Ω
$f_{H,3dB}$	Small-signal bandwidth	$i_{IN} = 50\ \mu\text{A}_{p-p}$ ⁽²⁾	2.2	2.8		GHz
$f_{L,3dB}$	Low-frequency, –3-dB bandwidth	–3 dB, input current $i_{IN} < 50\ \mu\text{A}_{p-p}$		40	70	kHz
$f_{H,3dB,RSSI}$	RSSI bandwidth			3.5		MHz
i_{N-IN}	Input referred RMS noise	50 kHz–4 GHz ⁽³⁾		465	590	nA
	Input referred noise current density			8.8		$\text{pA}/\sqrt{\text{Hz}}$
DJ	Deterministic jitter	$i_{IN} = 50\ \mu\text{A}_{p-p}$ (K28.5 pattern) ⁽⁴⁾		10	23	ps_{p-p}
		$i_{IN} = 100\ \mu\text{A}_{p-p}$ (K28.5 pattern) ⁽⁴⁾		10	30	
		$i_{IN} = 1\ \text{mA}_{p-p}$ (K28.5 pattern)		8	28	
		$i_{IN} = 2\ \text{mA}_{p-p}$ (K28.5 pattern)		13	42	
$V_{OUT,D,MAX}$	Maximum differential output voltage	Input current $i_{IN} = 1\ \text{mA}_{p-p}$	140	200	310	mV_{p-p}

- (1) The RSSI output is a current output, which requires a resistive load to ground (GND). The voltage gain can be adjusted for the intended application by choosing the external resistor. However, for proper operation of the ONET4291T, ensure that the voltage at RSSI never exceeds $V_{CC} - 0.65\text{ V}$.
- (2) The minimum small-signal bandwidth is specified over process corners, temperature, and supply voltage variation. The assumed photodiode capacitance is 0.2 pF. The bond-wire inductance is 0.8 nH. The small-signal bandwidth strongly depends on environmental parasitics. Careful attention to layout parasitics and external components is necessary to achieve optimal performance.
- (3) Input referred RMS noise is (RMS output noise)/(gain @ 100 MHz). The maximum input referred noise is specified over process corners, temperature, and supply voltage variation.
- (4) At small input currents a significant portion of the deterministic jitter (DJ) is caused by duty-cycle distortion (DCD) due to residual offset in the output signal. Because the TIA is not limiting, the DCD portion of the DJ is removed by the following limiting amplifier. The given maximum values include DCD as well as six-sigma margin.

TYPICAL CHARACTERISTICS

Typical operating condition is at $V_{CC} = 3.3\text{ V}$ and $T_A = 25^\circ\text{C}$.

UNFILTERED INPUT REFERRED NOISE
vs
AVERAGE INPUT CURRENT

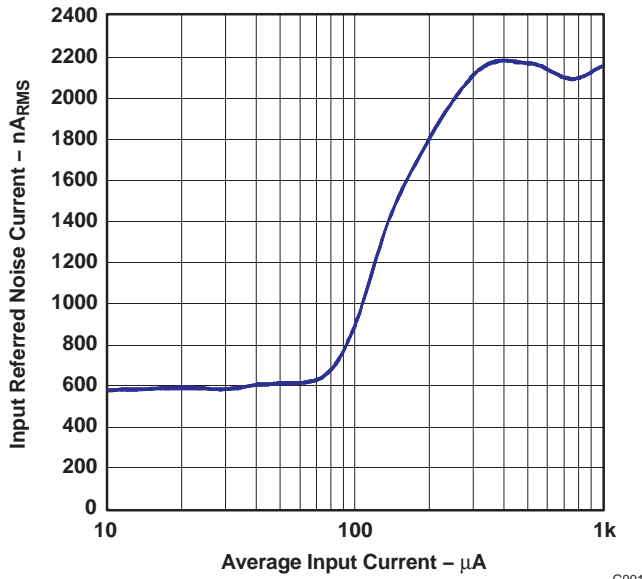


Figure 2.

G001

UNFILTERED INPUT REFERRED NOISE
vs
AMBIENT TEMPERATURE

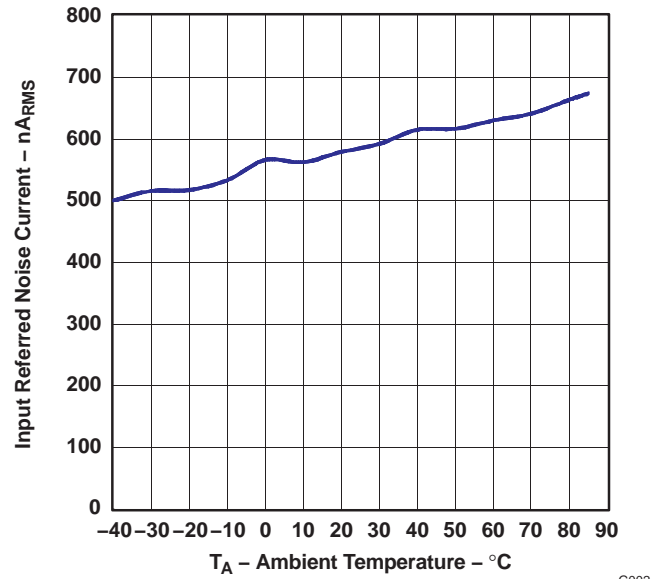


Figure 3.

G002

SMALL-SIGNAL TRANSIMPEDANCE
vs
AMBIENT TEMPERATURE

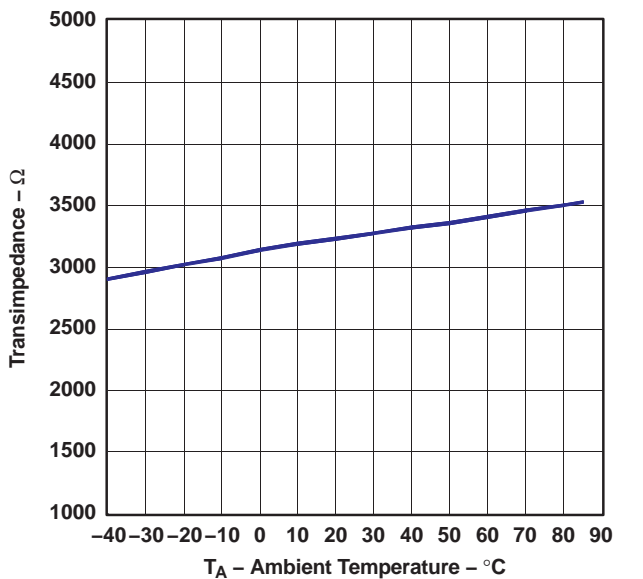


Figure 4.

G003

TRANSIMPEDANCE
vs
AVERAGE INPUT CURRENT

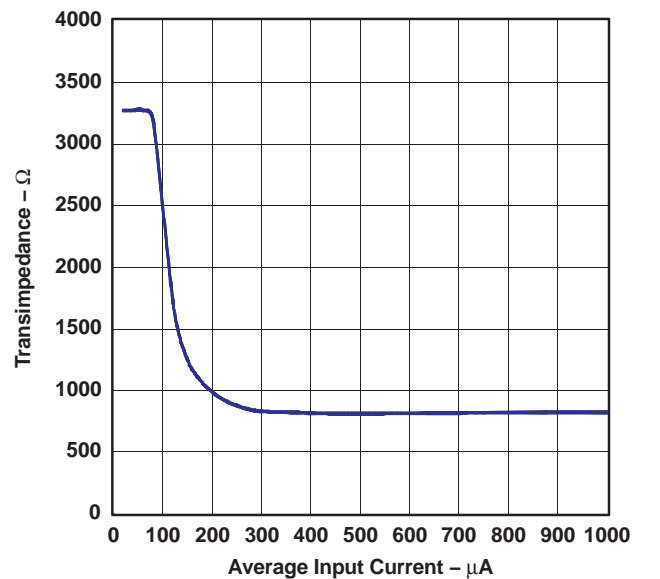


Figure 5.

G004

TYPICAL CHARACTERISTICS (continued)

Typical operating condition is at $V_{CC} = 3.3\text{ V}$ and $T_A = 25^\circ\text{C}$.

**SMALL-SIGNAL BANDWIDTH
vs
AMBIENT TEMPERATURE**

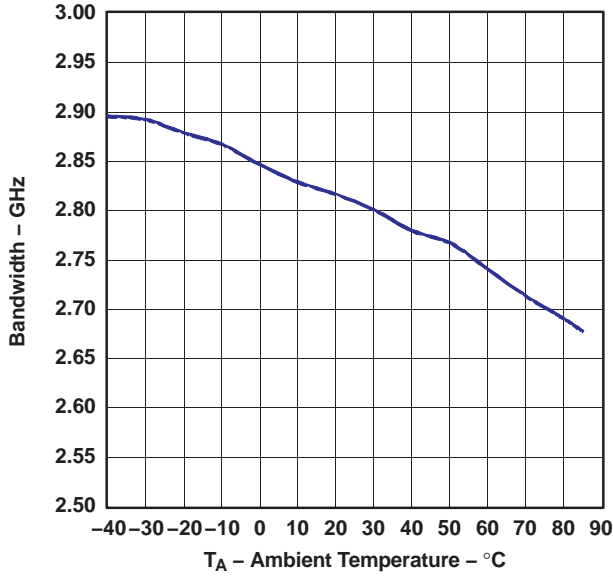


Figure 6.

G005

SMALL-SIGNAL TRANSFER CHARACTERISTICS

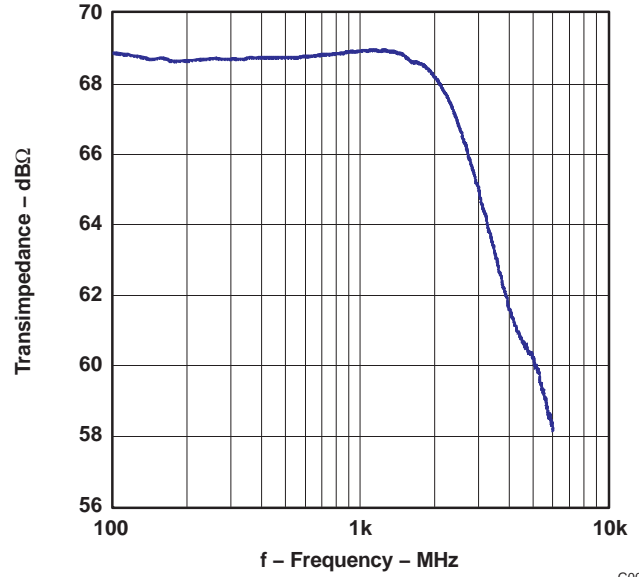


Figure 7.

G006

**RSSI OUTPUT CURRENT
vs
AVERAGE INPUT CURRENT**

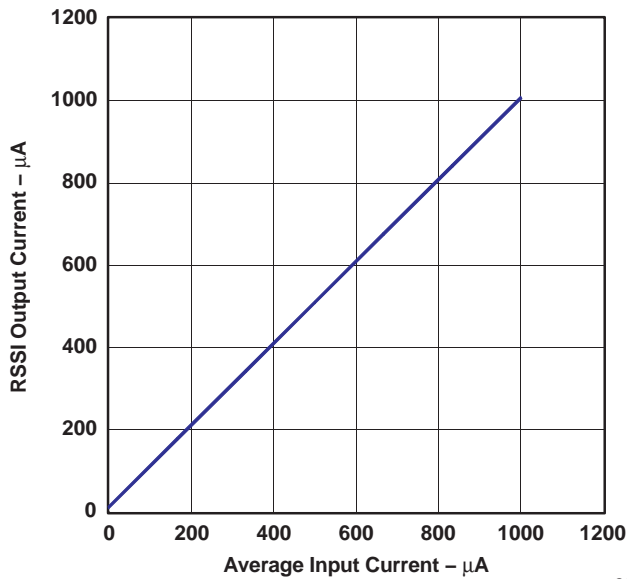


Figure 8.

G007

**DETERMINISTIC JITTER
vs
INPUT CURRENT**

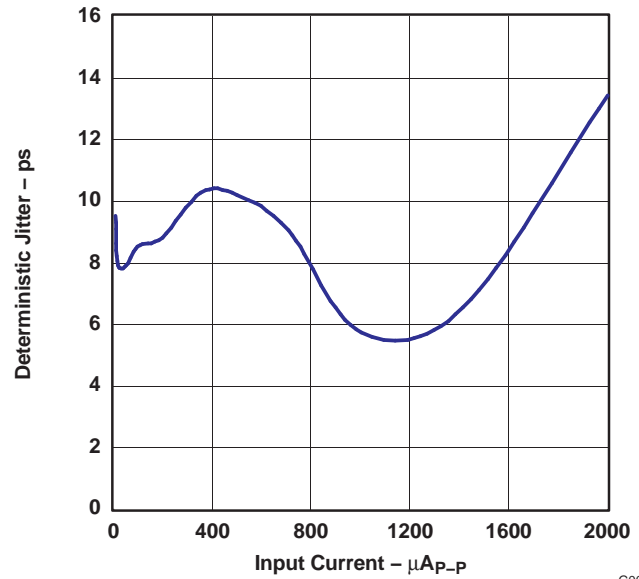


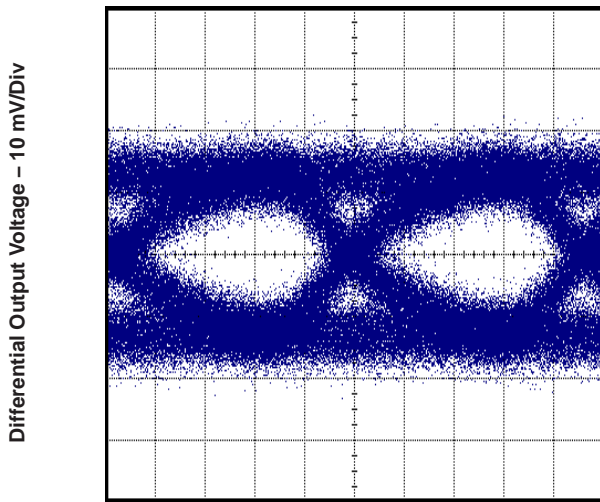
Figure 9.

G008

TYPICAL CHARACTERISTICS (continued)

Typical operating condition is at $V_{CC} = 3.3\text{ V}$ and $T_A = 25^\circ\text{C}$.

OUTPUT EYE DIAGRAM AT 4.25 Gbps AND $10\text{-}\mu\text{A}_{p-p}$ INPUT CURRENT

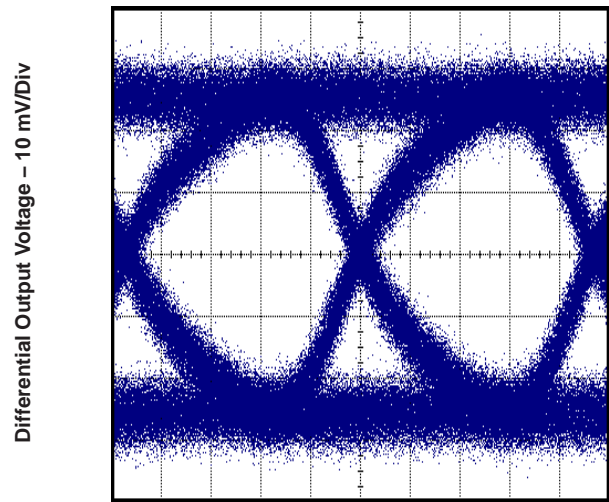


Time - 50 ps/Div

G009

Figure 10.

OUTPUT EYE DIAGRAM AT 4.25 Gbps AND $20\text{-}\mu\text{A}_{p-p}$ INPUT CURRENT

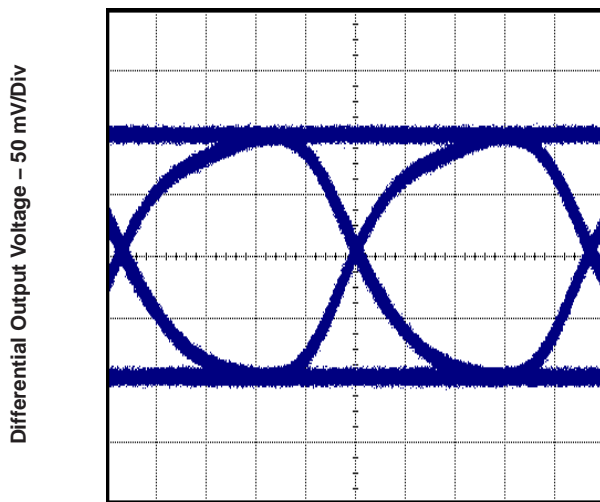


Time - 50 ps/Div

G010

Figure 11.

OUTPUT EYE DIAGRAM AT 4.25 Gbps AND $100\text{-}\mu\text{A}_{p-p}$ INPUT CURRENT

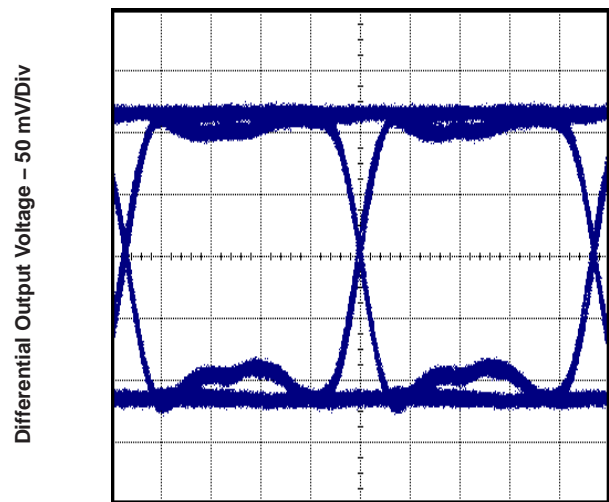


Time - 50 ps/Div

G011

Figure 12.

OUTPUT EYE DIAGRAM AT 4.25 Gbps AND 1-mA_{p-p} INPUT CURRENT



Time - 50 ps/Div

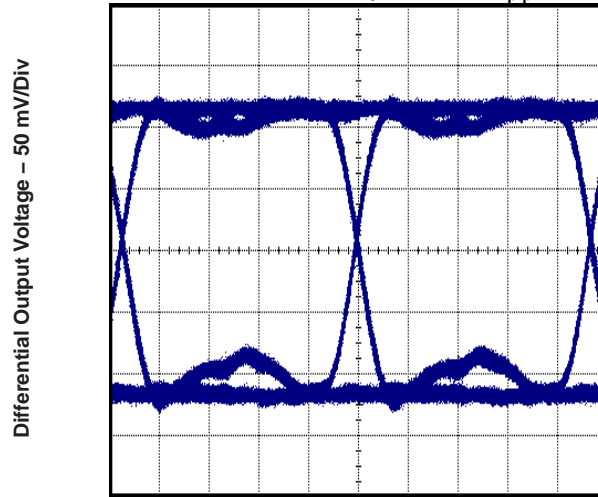
G012

Figure 13.

TYPICAL CHARACTERISTICS (continued)

Typical operating condition is at $V_{CC} = 3.3\text{ V}$ and $T_A = 25^\circ\text{C}$.

OUTPUT EYE DIAGRAM AT 4.25 Gbps AND 2-mA_{pp} INPUT CURRENT



Time - 50 ps/Div

Figure 14.

G013

APPLICATION INFORMATION

Figure 15 shows an application circuit for an ONET4291T being used in a typical fiber-optic receiver. The ONET4291T converts the electrical current generated by the PIN photodiode into a differential output voltage. The FILTER input provides a dc bias voltage for the PIN that is low-pass filtered by the combination of the internal 220-Ω resistor and 200-pF capacitor. Because the voltage drop across the 220-Ω resistor is sensed and used by the AGC circuit, the photodiode must be connected to a FILTER pad for the AGC to function correctly.

The RSSI output is used to mirror the photodiode average current and must be connected via a resistor to GND. The voltage gain can be adjusted for the intended application by choosing the external resistor. However, for proper operation of the ONET4291T, ensure that the voltage at RSSI never exceeds $V_{CC} - 0.65$ V. If the RSSI output is not used, it must be grounded.

The OUT+ and OUT- pads are internally terminated by 50-Ω pullup resistors to V_{CC} . The outputs must be ac-coupled (e.g., using $C_1 = C_2 = 0.1$ μF) to the succeeding device. An additional capacitor, C_{NBW} , which is differentially connected between the two output pins OUT+ and OUT-, can be used to limit the noise bandwidth and thus optimize the noise performance.

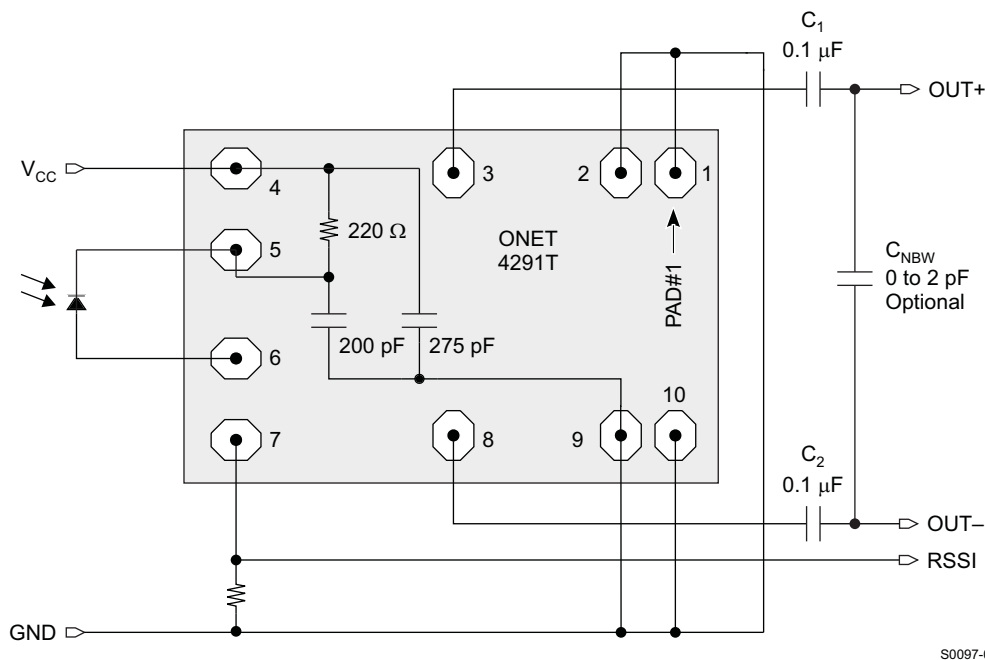


Figure 15. Basic Application Circuit

ASSEMBLY RECOMMENDATIONS

When packaging the ONET4291T, careful attention to parasitics and external components is necessary to achieve optimal performance. Recommendations that optimize performance include:

1. Minimize total capacitance on the IN pad by using a low-capacitance photodiode and paying attention to stray capacitances. Place the photodiode close to the ONET4291T die to minimize the bond wire length and thus the parasitic inductance.
2. Use identical termination and symmetrical transmission lines at the ac-coupled differential output pins OUT+ and OUT-. A differential capacitor C_{NBW} can be used to limit the noise bandwidth.
3. Use short bond-wire connections for the supply terminals V_{CC} and GND. Supply-voltage filtering is provided on-chip. Filtering can be improved by using an additional external capacitor.

CHIP DIMENSIONS AND PAD LOCATIONS

Overall chip dimensions and depiction of the bond-pad locations are given in Figure 16. Layout of the chip componentry is shown in Figure 17.

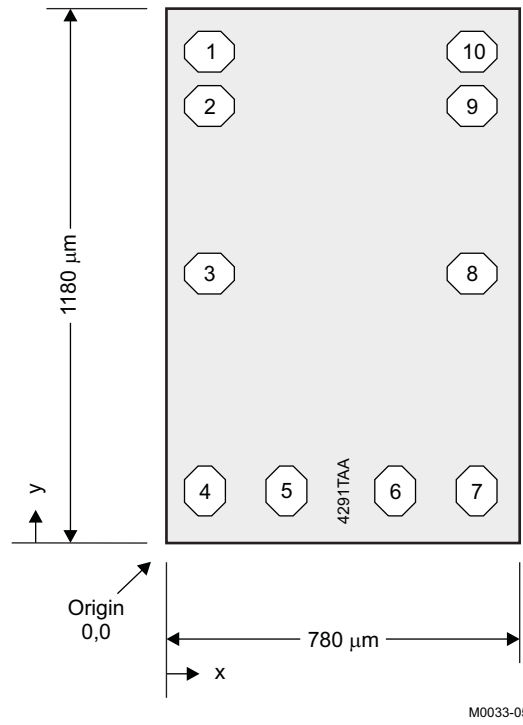


Figure 16. Chip Dimensions and Pad Locations

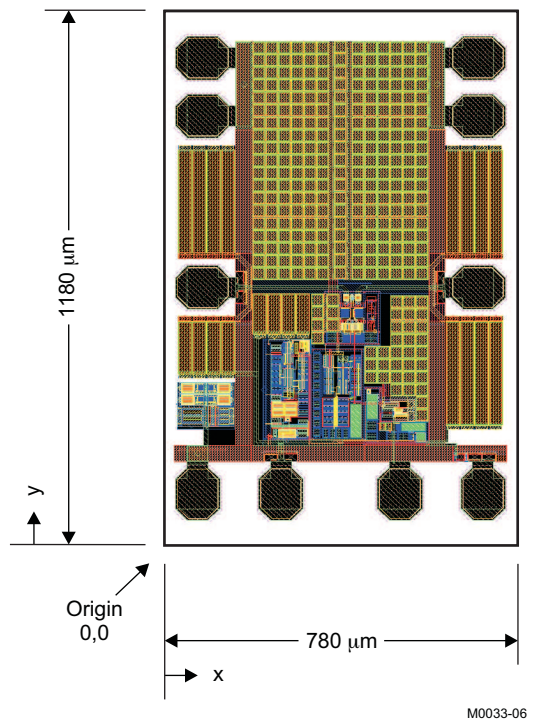


Figure 17. Chip Layout

Table 1. Pad Locations and Descriptions for the ONET4291T

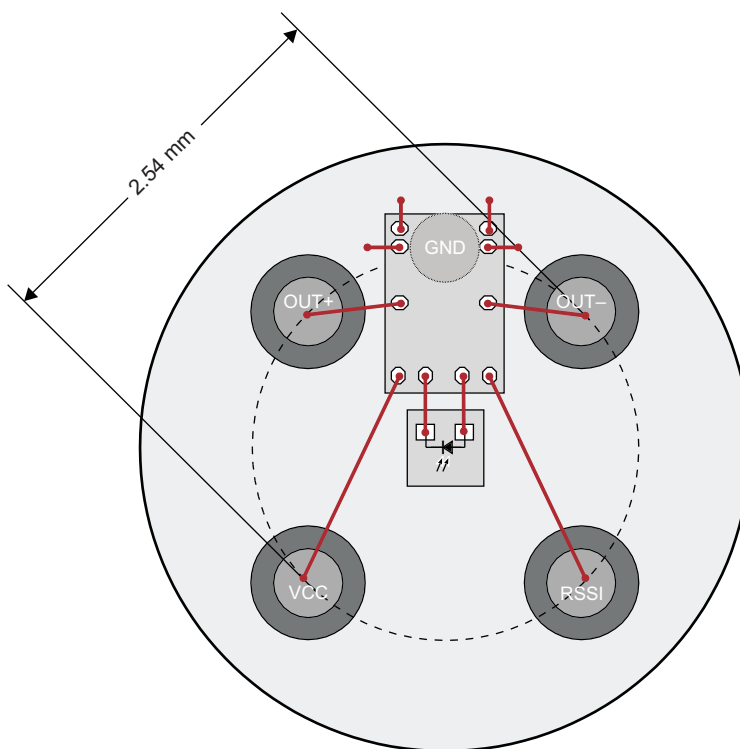
PAD	COORDINATES		SYMBOL	TYPE	DESCRIPTION
	x (μm)	y (μm)			
1	100	1063	GND	Supply	Circuit ground
2	100	938	GND	Supply	Circuit ground
3	100	570	OUT+	Analog output	Non-inverted data output
4	90	127	V _{CC}	Supply	3.3-V supply voltage
5	265	127	FILTER	Analog	Bias voltage for photodiode
6	515	127	IN	Analog input	Data input to TIA
7	690	127	RSSI	Analog output	RSSI output signal
8	680	570	OUT-	Analog output	Inverted data output
9	680	938	GND	Supply	Circuit ground
10	680	1063	GND	Supply	Circuit ground

DIE INFORMATION

Die size: 1180 μm × 780 μm
 Die thickness: 8 mils (203 μm)
 Pad metallization: 99.5% Al, 0.5% Cu
 Pad size: octagonal pads 120 μm × 100 μm
 Passivation composition: 6000-Å silicon nitride
 Backside contact: none
 Die ID: 4291TAA

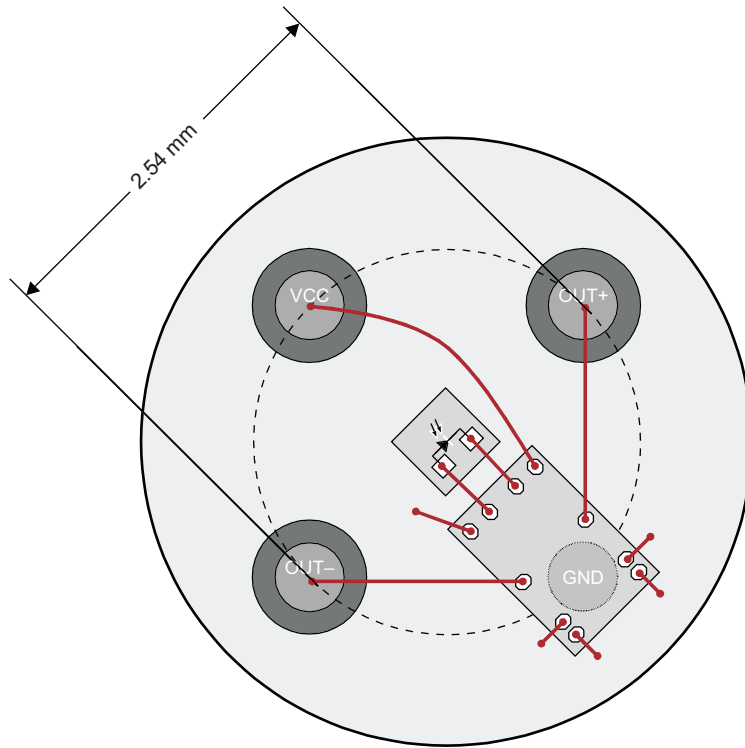
TO46 LAYOUT EXAMPLES

Examples for layouts (top view) in 5-pin and 4-pin TO46 headers are given in Figure 18 and Figure 19, respectively.



M0034-03

Figure 18. TO46 5-Pin Layout Example Using the ONET4291T



M0034-04

Figure 19. TO46 4-Pin Layout Example Using the ONET4291T

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
ONET4291TY	PREVIEW	DIESALE	Y	0	340	TBD	Call TI	Call TI	

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSELETE: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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放大器和线性器件	http://www.ti.com.cn/amplifiers	计算机及周边	www.ti.com.cn/computer
数据转换器	http://www.ti.com.cn/dataconverters	消费电子	www.ti.com/consumer-apps
DLP® 产品	www.dlp.com	能源	www.ti.com/energy
DSP - 数字信号处理器	http://www.ti.com.cn/dsp	工业应用	www.ti.com.cn/industrial
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